XP0111M

Silicon PNP epitaxial planar type

For switching/digital circuits

Features

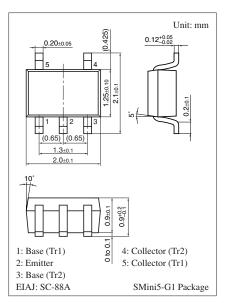
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR211M (UN211M) × 2

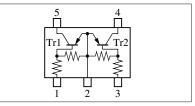
$\mathbf{I}_{a} = 25 \text{ C}$							
Symbol	Rating	Unit					
V _{CBO}	-50	V					
V _{CEO}	-50	V					
I _C	-100	mA					
P _T	150	mW					
Tj	150	°C					
T _{stg}	-55 to +150	°C					
	Symbol V _{CBO} V _{CEO} I _C P _T T _j	$\begin{tabular}{ c c c } \hline Symbol & Rating \\ \hline V_{CBO} & -50 \\ \hline V_{CEO} & -50 \\ \hline I_C & -100 \\ \hline P_T & 150 \\ \hline T_j & 150 \\ \hline \end{tabular}$					





Marking Symbol: EK

Internal Connection



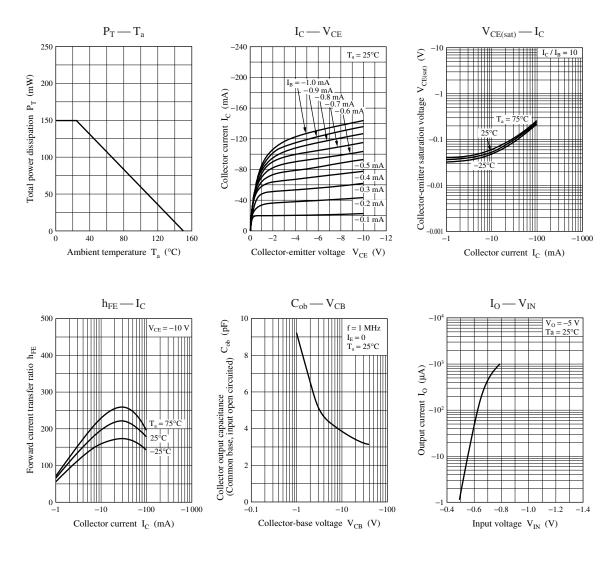
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{C} = -10 \ \mu A, \ I_{E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 V, I_C = 0$			- 0.2	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			_
h _{FE} Ratio *	h _{FE(Small}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
	/Large)					
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, \text{V}_{\text{B}} = -2.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	2.2	+30%	kΩ
Resistance ratio	R ₁ / R ₂			0.047		
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

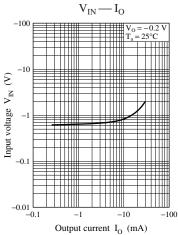
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

XP0111M







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